STRUCTURE AND METHOD TO PREVENT CHARGE DAMAGE FROM E-BEAM CURING PROCESS

Abstract

An example embodiment is a method of curing a film over a semiconductor structure. We provide a semiconductor structure comprised of a substrate and an interconnect structure. We provide a film over the semiconductor structure. We provide an electron source, an anode grid between the electron source and the semiconductor structure. We cure the film by exposing the film to an electron beam from the electron source that passes through the anode grid. We control the electron beam by controlling the bias voltage between the anode grid and the semiconductor structure. Another embodiment is a tool for curing a film.

Figure 1